Dual supply translating transceiver; auto direction sensing; 3-state

Rev. 7 — 9 April 2018

**Product data sheet** 

## 1. General description

The NTB0101 is a 1-bit, dual supply translating transceiver with auto direction sensing, that enables bidirectional voltage level translation. It features two 1-bit input-output ports (A and B), one output enable input (OE) and two supply pins ( $V_{CC(A)}$  and  $V_{CC(B)}$ ).  $V_{CC(A)}$  can be supplied at any voltage between 1.2 V and 3.6 V and  $V_{CC(B)}$  can be supplied at any voltage between 1.65 V, making the device suitable for translating between any of the low voltage nodes (1.2 V, 1.5 V, 1.8 V, 2.5 V, 3.3 V and 5.0 V).

Pins A and OE are referenced to V<sub>CC(A)</sub> and pin B is referenced to V<sub>CC(B)</sub>. A LOW level at pin OE causes the outputs to assume a high-impedance OFF-state. This device is fully specified for partial power-down applications using I<sub>OFF</sub>. The I<sub>OFF</sub> circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

## 2. Features and benefits

- Wide supply voltage range:
  - ◆ V<sub>CC(A)</sub>: 1.2 V to 3.6 V and V<sub>CC(B)</sub>: 1.65 V to 5.5 V
- I<sub>OFF</sub> circuitry provides partial Power-down mode operation
- Inputs accept voltages up to 5.5 V
- ESD protection:
  - ◆ HBM JESD22-A114E Class 2 exceeds 2500 V for A port
  - HBM JESD22-A114E Class 3B exceeds 15000 V for B port
  - MM JESD22-A115-A exceeds 200 V
  - CDM JESD22-C101E exceeds 1500 V
- Latch-up performance exceeds 100 mA per JESD 78B Class II
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



### 3. Ordering information

Type number	Topside	Package	Package						
	marking <sup>[1]</sup>	Name	Description	Version					
NTB0101GW	t1	SC-88	plastic surface-mounted package; 6 leads	SOT363					
NTB0101GM	t1	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; $1 \times 1.45 \times 0.5$ mm body	SOT886					
NTB0101GF	t1	XSON6	plastic extremely thin small outline package; no leads; 6 terminals; $1 \times 1 \times 0.5$ mm body	SOT891					
NTB0101GS	t1	XSON6	extremely thin small outline package; no leads; 6 terminals; $1.0 \times 1.0 \times 0.35$ mm body	SOT1202					
NTB0101GS1	T1	X2SON6	plastic super thin small outline package; no leads; 6 terminals; $1.0 \times 1.0 \times 0.32$ mm body	SOT1202-2					
NTB0101GN	t1	XSON6	extremely thin small outline package; no leads; 6 terminals; $0.9 \times 1.0 \times 0.35$ mm body	SOT1115					

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

## 3.1 Ordering options

#### **Ordering options** Table 2.

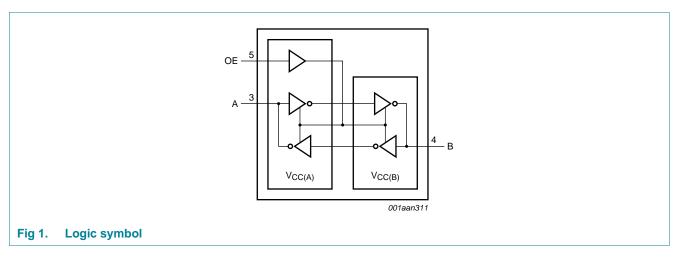
Type number	Orderable part number	Package	Packing method	Minimum order qty	Temperature
NTB0101GW <sup>[3]</sup>	NTB0101GW,125	SC-88	REEL 7" Q3/T4 *STANDARD MARK	3000	$T_{amb} = -40 \text{ °C to } +125 \text{ °C}$
NTB0101GM	NTB0101GM,115	XSON6	REEL 7" Q1/T1 *STANDARD MARK SMD	5000	$T_{amb} = -40 \text{ °C to } +125 \text{ °C}$
NTB0101GF <sup>[1]</sup>	NTB0101GF,132	XSON6	REEL 7" Q1/T1,Q3/T4 *STANDARD MARK SMD	5000	$T_{amb} = -40 \text{ °C to } +125 \text{ °C}$
NTB0101GS <sup>[2]</sup>	NTB0101GS,132	XSON6	REEL 7" Q1/T1,Q3/T4 *STANDARD MARK SMD	5000	$T_{amb} = -40 \text{ °C to } +125 \text{ °C}$
NTB0101GS1	NTB0101GS1Z	X2SON6	REEL 7" Q2/T3 *STANDARD MARK	10000	$T_{amb} = -40 \text{ °C to } +125 \text{ °C}$
NTB0101GN[1]	NTB0101GN,132	XSON6	REEL 7" Q1/T1,Q3/T4 *STANDARD MARK SMD	5000	$T_{amb} = -40 \ ^{\circ}C \ to +125 \ ^{\circ}C$

[1] Discontinued with 24 Apr 2018 Last Time Buy and 24 Jul 2018 Last Time Ship date.

[2] Discontinued with 31 Aug 2018 Last Time Buy and 30 Nov 2018 Last Time Ship date.

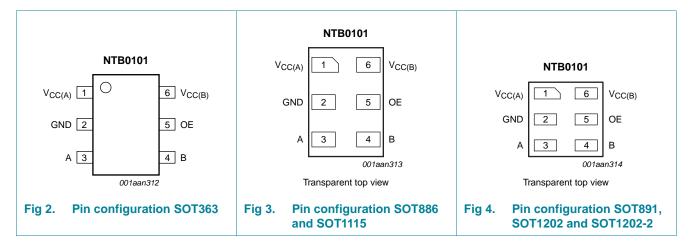
[3] Not recommend for new design.

## 4. Functional diagram



## 5. Pinning information

## 5.1 Pinning



## 5.2 Pin description

Symbol	Pin	Description
V <sub>CC(A)</sub>	1	supply voltage A
GND	2	ground (0 V)
A	3	data input or output (referenced to V <sub>CC(A)</sub> )
В	4	data input or output (referenced to V <sub>CC(B)</sub> )
OE	5	output enable input (active HIGH; referenced to $V_{CC(A)}$ )
V <sub>CC(B)</sub>	6	supply voltage B

## 6. Functional description

## Table 4. Function table<sup>[1]</sup>

Supply voltage		Input	Input/output		
V <sub>CC(A)</sub>	V <sub>CC(B)</sub>	OE	Α	В	
1.2 V to V <sub>CC(B)</sub>	1.65 V to 5.5 V	L	Z	Z	
1.2 V to V <sub>CC(B)</sub>	1.65 V to 5.5 V	Н	input or output	output or input	
GND <sup>[2]</sup>	GND <sup>[2]</sup>	Х	Z	Z	

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

[2] When either  $V_{CC(A)}$  or  $V_{CC(B)}$  is at GND level, the device goes into Power-down mode.

## 7. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CC(A)</sub>	supply voltage A			-0.5	+6.5	V
V <sub>CC(B)</sub>	supply voltage B			-0.5	+6.5	V
VI	input voltage		[1]	-0.5	+6.5	V
Vo	output voltage	Active mode	[1][2][3]	-0.5	V <sub>CCO</sub> + 0.5	V
		Power-down or 3-state mode	[1]	-0.5	+6.5	V
I <sub>IK</sub>	input clamping current	V <sub>1</sub> < 0 V		-50	-	mA
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < 0 V		-50	-	mA
lo	output current	$V_{O} = 0 V$ to $V_{CCO}$	[2]	-	±50	mA
I <sub>CC</sub>	supply current	I <sub>CC(A)</sub> or I <sub>CC(B)</sub>		-	100	mA
I <sub>GND</sub>	ground current			-100	-	mA
T <sub>stg</sub>	storage temperature			-65	+150	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40 \text{ °C to } +125 \text{ °C}$	[4]	-	250	mW

[1] The minimum input and minimum output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] V<sub>CCO</sub> is the supply voltage associated with the output.

[3]  $V_{CCO}$  + 0.5 V should not exceed 6.5 V.

[4] For SC-88 and SC-74A packages: above 87.5 °C the value of P<sub>tot</sub> derates linearly with 4.0 mW/K. For XSON6 packages: above 118 °C the value of P<sub>tot</sub> derates linearly with 7.8 mW/K.

## 8. Recommended operating conditions

Table 6. Recommended operating conditions <sup>[1][2]</sup>	Table 6.	Recommended	operating	conditions <sup>[1][2]</sup>
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Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC(A)</sub>	supply voltage A		1.2	3.6	V
V <sub>CC(B)</sub>	supply voltage B		1.65	5.5	V
VI	input voltage		0	5.5	V

Symbol	Parameter	Conditions	Min	Max	Unit
Vo	output voltage	Power-down or 3-state mode; $V_{CC(A)} = 1.2 V \text{ to } 3.6 V;$ $V_{CC(B)} = 1.65 V \text{ to } 5.5 V$			
		A port	0	3.6	V
		B port	0	5.5	V
T <sub>amb</sub>	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	$V_{CC(A)} = 1.2 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$	-	40	ns/V

### Table 6. Recommended operating conditions<sup>[1][2]</sup> ...continued

[1] The A and B sides of an unused I/O pair must be held in the same state, both at  $V_{CCI}$  or both at GND.

[2]  $V_{CC(A)}$  must be less than or equal to  $V_{CC(B)}$ .

## 9. Static characteristics

### Table 7. Typical static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); T<sub>amb</sub> = 25 °C.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>OH</sub>	HIGH-level output voltage	A port; $V_{CC(A)} = 1.2 \text{ V}$ ; $I_0 = -20 \mu\text{A}$		-	1.1	-	V
V <sub>OL</sub>	LOW-level output voltage	A port; $V_{CC(A)} = 1.2 \text{ V}$ ; $I_0 = 20 \mu\text{A}$		-	0.09	-	V
I <sub>I</sub>	input leakage current	OE input; V <sub>I</sub> = 0 V to 3.6 V; V <sub>CC(A)</sub> = 1.2 V to 3.6 V; V <sub>CC(B)</sub> = 1.65 V to 5.5 V		-	-	±1	μA
I <sub>OZ</sub>	OFF-state output current	A or B port; $V_O = 0$ V to $V_{CCO}$ ; $V_{CC(A)} = 1.2$ V to 3.6 V; $V_{CC(B)} = 1.65$ V to 5.5 V	[1]	-	-	±1	μA
I <sub>OFF</sub>	power-off leakage current	A port; V <sub>1</sub> or V <sub>O</sub> = 0 V to 3.6 V; V <sub>CC(A)</sub> = 0 V; V <sub>CC(B)</sub> = 0 V to 5.5 V		-	-	±1	μA
		B port; V <sub>I</sub> or V <sub>O</sub> = 0 V to 5.5 V; V <sub>CC(B)</sub> = 0 V; V <sub>CC(A)</sub> = 0 V to 3.6 V		-	-	±1	μA
Cı	input capacitance	OE input; $V_{CC(A)}$ = 1.2 V to 3.6 V; $V_{CC(B)}$ = 1.65 V to 5.5 V		-	1.0	-	pF
C <sub>I/O</sub>	input/output	A port; $V_{CC(A)} = 1.2$ V to 3.6 V; $V_{CC(B)} = 1.65$ V to 5.5 V		-	4.0	-	pF
	capacitance	B port; $V_{CC(A)} = 1.2$ V to 3.6 V; $V_{CC(B)} = 1.65$ V to 5.5 V		-	7.5	-	pF

[1]  $V_{CCO}$  is the supply voltage associated with the output.

[2] V<sub>CCI</sub> is the supply voltage associated with the input.

### Table 8.Typical supply current

At recommended operating conditions; voltages are referenced to GND (ground = 0 V); T<sub>amb</sub> = 25 °C.

V <sub>CC(A)</sub>	V <sub>CC(B)</sub>									
	1.8 V		2.5 V	2.5 V		3.3 V		5.0 V		
	I <sub>CC(A)</sub>	I <sub>CC(B)</sub>								
1.2 V	10	10	10	10	10	20	10	1050	nA	
1.5 V	10	10	10	10	10	10	10	650	nA	

### Table 8. Typical ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V);  $T_{amb} = 25$  °C.

V <sub>CC(A)</sub>	V <sub>CC(B)</sub>	V <sub>CC(B)</sub>										
	1.8 V		2.5 V	2.5 V		3.3 V		5.0 V				
	I <sub>CC(A)</sub>	I <sub>CC(B)</sub>										
1.8 V	10	10	10	10	10	10	10	350	nA			
2.5 V	-	-	10	10	10	10	10	40	nA			
3.3 V	-	-	-	-	10	10	10	10	nA			

### Table 9. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		-40 °C to	o +85 °C	–40 °C to	+125 °C	Unit
				Min	Max	Min	Max	
VIH	HIGH-level	A or B port and OE input	[1]					
	input voltage	$V_{CC(A)} = 1.2 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$		0.65V <sub>CCI</sub>	-	0.65V <sub>CCI</sub>	-	V
VIL	LOW-level	A or B port and OE input	[1]					
	input voltage	$V_{CC(A)} = 1.2 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$		-	0.35V <sub>CCI</sub>	-	0.35V <sub>CCI</sub>	V
V <sub>OH</sub>	HIGH-level	I <sub>O</sub> = -20 μA	[2]					
	output voltage	A port; $V_{CC(A)} = 1.4$ V to 3.6 V		$V_{CCO}-0.4$	-	$V_{CCO}-0.4$	-	V
		B port; $V_{CC(B)} = 1.65$ V to 5.5 V		$V_{CCO}-0.4$	-	$V_{CCO}-0.4$	-	V
V <sub>OL</sub>	LOW-level	I <sub>O</sub> = 20 μA	[2]					
	output voltage	A port; $V_{CC(A)} = 1.4$ V to 3.6 V		-	0.4	-	0.4	V
		B port; $V_{CC(B)} = 1.65$ V to 5.5 V		-	0.4	-	0.4	V
I	input leakage current	$\begin{array}{l} \text{OE input; V}_{I} = 0 \text{ V to } 3.6 \text{ V;} \\ \text{V}_{\text{CC}(A)} = 1.2 \text{ V to } 3.6 \text{ V;} \\ \text{V}_{\text{CC}(B)} = 1.65 \text{ V to } 5.5 \text{ V} \end{array}$		-	±2	-	±5	μΑ
I <sub>OZ</sub>	OFF-state output current	A or B port; $V_O = 0$ V or $V_{CCO}$ ; $V_{CC(A)} = 1.2$ V to 3.6 V; $V_{CC(B)} = 1.65$ V to 5.5 V	[2]	-	±2	-	±10	μΑ
I <sub>OFF</sub>	power-off leakage	A port; V <sub>1</sub> or V <sub>0</sub> = 0 V to 3.6 V; V <sub>CC(A)</sub> = 0 V; V <sub>CC(B)</sub> = 0 V to 5.5 V		-	±2	-	±10	μA
	current	$            B \mbox{ port; } V_{I} \mbox{ or } V_{O} = 0 \mbox{ V to } 5.5 \mbox{ V; } \\ V_{CC(B)} = 0 \mbox{ V; } V_{CC(A)} = 0 \mbox{ V to } 3.6 \mbox{ V } $		-	±2	-	±10	μΑ

### Table 9. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		–40 °C t	o +85 °C	–40 °C to	o +125 °C	Unit
				Min	Max	Min	Max	
I <sub>CC</sub>	supply current	$V_{I} = 0 V \text{ or } V_{CCI}; I_{O} = 0 A$	[1]					
		I <sub>CC(A)</sub>						
		OE = LOW; V <sub>CC(A)</sub> = 1.4 V to 3.6 V; V <sub>CC(B)</sub> = 1.65 V to 5.5 V		-	3	-	15	μA
		$\begin{array}{l} {\sf OE} = {\sf HIGH}; \\ {\sf V}_{{\sf CC}({\sf A})} = 1.4 \; {\sf V} \; {\sf to} \; 3.6 \; {\sf V}; \\ {\sf V}_{{\sf CC}({\sf B})} = 1.65 \; {\sf V} \; {\sf to} \; 5.5 \; {\sf V} \end{array}$		-	3	-	20	μA
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$		-	2	-	15	μΑ
		$V_{CC(A)} = 0 V; V_{CC(B)} = 5.5 V$		-	-2	-	-15	μΑ
		I <sub>CC(B)</sub>						
		OE = LOW; V <sub>CC(A)</sub> = 1.4 V to 3.6 V; V <sub>CC(B)</sub> = 1.65 V to 5.5 V		-	5	-	15	μA
		OE = HIGH; V <sub>CC(A)</sub> = 1.4 V to 3.6 V; V <sub>CC(B)</sub> = 1.65 V to 5.5 V		-	5	-	20	μA
		$V_{CC(A)} = 3.6 \text{ V}; V_{CC(B)} = 0 \text{ V}$		-	-2	-	-15	μΑ
		$V_{CC(A)} = 0 V; V_{CC(B)} = 5.5 V$		-	2	-	15	μΑ
		$I_{CC(A)} + I_{CC(B)}$						
		$V_{CC(A)} = 1.4 \text{ V to } 3.6 \text{ V};$ $V_{CC(B)} = 1.65 \text{ V to } 5.5 \text{ V}$		-	8	-	40	μΑ

[1]  $V_{CCI}$  is the supply voltage associated with the input.

[2] V<sub>CCO</sub> is the supply voltage associated with the output.

## **10.** Dynamic characteristics

## Table 10. Typical dynamic characteristics for temperature 25 °C<sup>[1]</sup>

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for waveforms see Figure 5 and Figure 6.

Symbol	Parameter	Conditions			Vc	С(В)		Unit
				1.8 V	2.5 V	3.3 V	5.0 V	
$V_{CC(A)} = $	I.2 V; T <sub>amb</sub> = 25 °C							
t <sub>pd</sub>	propagation delay	A to B		5.9	4.8	4.4	4.2	ns
		B to A		5.6	4.8	4.5	4.4	ns
t <sub>en</sub>	enable time	OE to A, B		0.5	0.5	0.5	0.5	μS
t <sub>dis</sub>	disable time	OE to A; no external load	[2]	6.9	6.9	6.9	6.9	ns
		OE to B; no external load	[2]	9.5	8.6	8.5	8.0	ns
		OE to A		81	69	83	68	ns
		OE to B		81	69	83	68	ns

### Table 10. Typical dynamic characteristics for temperature 25 °C<sup>[1]</sup> ... continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for waveforms see Figure 5 and Figure 6.

Symbol	Parameter	Conditions		V <sub>CC(B)</sub>					
			1.8 V	2.5 V	3.3 V	5.0 V			
t <sub>t</sub>	transition time	A port	4.0	4.0	4.1	4.1	ns		
		B port	2.6	2.0	1.7	1.4	ns		
t <sub>W</sub>	pulse width	data inputs	15	13	13	13	ns		
f <sub>data</sub>	data rate		70	80	80	80	Mbps		

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

 $t_{en}$  is the same as  $t_{PZL}$  and  $t_{PZH}$ .

 $t_{\text{dis}}$  is the same as  $t_{\text{PLZ}}$  and  $t_{\text{PHZ}}.$ 

 $t_t$  is the same as  $t_{\mathsf{THL}}$  and  $t_{\mathsf{TLH}}$ 

[2] Delay between OE going LOW and when the outputs are actually disabled.

### Table 11. Dynamic characteristics for temperature range –40 °C to +85 °C[1]

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6.

Symbol	Parameter	Conditions					Vcc	С(В)				Unit
				1.8 V ±	0.15 V	2.5 V ±	0.2 V	3.3 V :	± 0.3 V	5.0 V	± 0.5 V	
				Min	Max	Min	Max	Min	Max	Min	Max	
V <sub>CC(A)</sub> =	$\textbf{1.5 V} \pm \textbf{0.1 V}$											
t <sub>pd</sub>	propagation	A to B		1.4	12.9	1.2	10.1	1.1	10.0	0.8	9.9	ns
	delay	B to A		0.9	14.2	0.7	12.0	0.4	11.7	0.3	13.7	ns
t <sub>en</sub>	enable time	OE to A, B		-	1.0	-	1.0	-	1.0	-	1.0	μs
t <sub>dis</sub>	disable time	OE to A; no external load	[2]	1.0	11.9	1.0	11.9	1.0	11.9	1.0	11.9	ns
		OE to B; no external load	[2]	1.0	16.9	1.0	15.2	1.0	14.1	1.0	13.8	ns
		OE to A		-	320	-	260	-	260	-	280	ns
		OE to B		-	200	-	200	-	200	-	200	ns
t <sub>t</sub>	transition	A port		0.9	5.1	0.9	5.1	0.9	5.1	0.9	5.1	ns
	time	B port		0.9	4.7	0.6	3.2	0.5	2.5	0.4	2.7	ns
t <sub>W</sub>	pulse width	data inputs		25	-	25	-	25	-	25	-	ns
f <sub>data</sub>	data rate			-	40	-	40	-	40	-	40	Mbps
V <sub>CC(A)</sub> =	$\textbf{1.8 V} \pm \textbf{0.15 V}$		-									
t <sub>pd</sub>	propagation	A to B		1.6	11.0	1.4	7.7	1.3	6.8	1.2	6.5	ns
	delay	B to A		1.5	12.0	1.3	8.4	1.0	7.6	0.9	7.1	ns
t <sub>en</sub>	enable time	OE to A, B		-	1.0	-	1.0	-	1.0	-	1.0	μs
t <sub>dis</sub>	disable time	OE to A; no external load	[2]	1.0	11.0	1.0	11.0	1.0	11.0	1.0	11.0	ns
		OE to B; no external load	[2]	1.0	15.4	1.0	13.5	1.0	12.4	1.0	12.1	ns
		OE to A		-	260	-	230	-	230	-	230	ns
		OE to B		-	200	-	200	-	200	-	200	ns
tt	transition	A port		0.8	4.1	0.8	4.1	0.8	4.1	0.8	4.1	ns
	time	B port		0.9	4.7	0.6	3.2	0.5	2.5	0.4	2.7	ns
t <sub>W</sub>	pulse width	data inputs		20	-	17	-	17	-	17	-	ns
f <sub>data</sub>	data rate			-	49	-	60	-	60	-	60	Mbps
	1		1	1	1	1	1	1	1	1	1	1

Symbol	Parameter	Conditions					Vcc	(В)				Unit
				1.8 V ±	0.15 V	2.5 V :	± 0.2 V	3.3 V :	± 0.3 V	5.0 V	± 0.5 V	
				Min	Max	Min	Max	Min	Max	Min	Max	
V <sub>CC(A)</sub> =	$2.5 \ \mathbf{V} \pm 0.2 \ \mathbf{V}$				1	1	1		1			1
t <sub>pd</sub>	propagation	A to B		-	-	1.1	6.3	1.0	5.2	0.9	4.7	ns
	delay	B to A		-	-	1.2	6.6	1.1	5.1	0.9	4.4	ns
t <sub>en</sub>	enable time	OE to A, B		-	-	-	1.0	-	1.0	-	1.0	μs
t <sub>dis</sub>	disable time	OE to A; no external load	[2]	-	-	1.0	9.2	1.0	9.2	1.0	9.2	ns
		OE to B; no external load	[2]	-	-	1.0	11.9	1.0	10.7	1.0	10.2	ns
		OE to A		-	-	-	200	-	200	-	200	ns
		OE to B		-	-	-	200	-	200	-	200	ns
t <sub>t</sub>	transition	A port		-	-	0.7	3.0	0.7	3.0	0.7	3.0	ns
	time	B port		-	-	0.7	3.2	0.5	2.5	0.4	2.7	ns
t <sub>W</sub>	pulse width	data inputs		-	-	12	-	10	-	10	-	ns
f <sub>data</sub>	data rate			-	-	-	85	-	100	-	100	Mbps
$V_{CC(A)} =$	3.3 V $\pm$ 0.3 V											
t <sub>pd</sub>	propagation	A to B		-	-	-	-	0.9	4.7	0.8	4.0	ns
	delay	B to A		-	-	-	-	1.0	4.9	0.9	3.8	ns
t <sub>en</sub>	enable time	OE to A, B		-	-	-	-	-	1.0	-	1.0	μs
t <sub>dis</sub>	disable time	OE to A; no external load	[2]	-	-	-	-	1.0	9.2	1.0	9.2	ns
		OE to B; no external load	[2]	-	-	-	-	1.0	10.1	1.0	9.6	ns
		OE to A		-	-	-	-	-	260	-	260	ns
		OE to B		-	-	-	-	-	200	-	200	ns
t <sub>t</sub>	transition	A port		-	-	-	-	0.7	2.5	0.7	2.5	ns
	time	B port		-	-	-	-	0.5	2.5	0.4	2.7	ns
t <sub>W</sub>	pulse width	data inputs		-	-	-	-	10	-	10	-	ns
f <sub>data</sub>	data rate			-	-	-	-	-	100	-	100	Mbps

### Table 11. Dynamic characteristics for temperature range -40 °C to +85 °C<sup>[1]</sup> ...continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6.

[2] Delay between OE going LOW and when the outputs are actually disabled.

## Table 12. Dynamic characteristics for temperature range -40 °C to +125 °C<sup>[1]</sup>

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6.

Symbol	Parameter	Conditions					Vcc	С(В)				Unit
				1.8 V ±	0.15 V	2.5 V :	± 0.2 V	3.3 V :	± 0.3 V	5.0 V ±	± 0.5 V	
				Min	Max	Min	Max	Min	Max	Min	Max	-
V <sub>CC(A)</sub> =	$\textbf{1.5 V} \pm \textbf{0.1 V}$											
t <sub>pd</sub>	propagation	A to B		1.4	15.9	1.2	13.1	1.1	13.0	0.8	12.9	ns
	delay	B to A		0.9	17.2	0.7	15.0	0.4	14.7	0.3	16.7	ns
t <sub>en</sub>	enable time	OE to A, B		-	1.0	-	1.0	-	1.0	-	1.0	μS
t <sub>dis</sub>	disable time	OE to A; no external load	[2]	1.0	12.5	1.0	12.5	1.0	12.5	1.0	12.5	ns
		OE to B; no external load	[2]	1.0	18.1	1.0	16.2	1.0	14.9	1.0	14.6	ns
		OE to A		-	340	-	280	-	280	-	300	ns
		OE to B		-	220	-	220	-	220	-	220	ns
t <sub>t</sub>	transition	A port		0.9	7.1	0.9	7.1	0.9	7.1	0.9	7.1	ns
	time	B port		0.9	6.5	0.6	5.2	0.5	4.8	0.4	4.7	ns
t <sub>W</sub>	pulse width	data inputs		25	-	25	-	25	-	25	-	ns
f <sub>data</sub>	data rate			-	40	-	40	-	40	-	40	Mbps
V <sub>CC(A)</sub> =	$\textbf{1.8 V} \pm \textbf{0.15 V}$											
t <sub>pd</sub>	propagation	A to B		1.6	14.0	1.4	10.7	1.3	9.8	1.2	9.5	ns
	delay	B to A		1.5	15.0	1.3	11.4	1.0	10.6	0.9	10.1	ns
	OE to A, B		-	1.0	-	1.0	-	1.0	-	1.0	μS	
t <sub>dis</sub>	disable time	OE to A; no external load	[2]	1.0	11.5	1.0	11.5	1.0	11.5	1.0	11.5	ns
		OE to B; no external load	[2]	1.0	16.5	1.0	14.5	1.0	13.3	1.0	12.7	ns
		OE to A		-	280	-	250	-	250	-	250	ns
		OE to B		-	220	-	220	-	220	-	220	ns
t <sub>t</sub>	transition	A port		0.8	6.2	0.8	6.1	0.8	6.1	0.8	6.1	ns
	time	B port		0.9	5.8	0.6	5.2	0.5	4.8	0.4	4.7	ns
t <sub>W</sub>	pulse width	data inputs		22	-	19	-	19	-	19	-	ns
f <sub>data</sub>	data rate			-	45	-	55	-	55	-	55	Mbps
V <sub>CC(A)</sub> =	$\textbf{2.5 V} \pm \textbf{0.2 V}$											
t <sub>pd</sub>	propagation	A to B		-	-	1.1	9.3	1.0	8.2	0.9	7.7	ns
	delay	B to A		-	-	1.2	9.6	1.1	8.1	0.9	7.4	ns
t <sub>en</sub>	enable time	OE to A, B		-	-	-	1.0	-	1.0	-	1.0	μS
t <sub>dis</sub>	disable time	OE to A; no external load	[2]	-	-	1.0	9.6	1.0	9.6	1.0	9.6	ns
		OE to B; no external load	[2]	-	-	1.0	12.6	1.0	11.4	1.0	10.8	ns
		OE to A		-	-	-	220	-	220	-	220	ns
		OE to B		-	-	-	220	-	220	-	220	ns
t <sub>t</sub>	transition	A port		-	-	0.7	5.0	0.7	5.0	0.7	5.0	ns
	time	B port		-	-	0.7	4.6	0.5	4.8	0.4	4.7	ns
t <sub>W</sub>	pulse width	data inputs;		-	-	14	-	13	-	10	-	ns
f <sub>data</sub>	data rate			-	-	-	75	-	80	-	100	Mbps

**Product data sheet** 

Symbol	Parameter	Conditions					Vcc	C(B)				Unit
				1.8 V ±	0.15 V	2.5 V :	± 0.2 V	3.3 V :	± 0.3 V	5.0 V :	± 0.5 V	
				Min	Max	Min	Max	Min	Max	Min	Max	
V <sub>CC(A)</sub> =	$3.3 \text{ V} \pm 0.3 \text{ V}$											
t <sub>pd</sub>	propagation	A to B		-	-	-	-	0.9	7.7	0.8	7.0	ns
	delay	B to A		-	-	-	-	1.0	7.9	0.9	6.8	ns
t <sub>en</sub>	enable time	OE to A, B		-	-	-	-	-	1.0	-	1.0	μs
t <sub>dis</sub>	disable time	OE to A; no external load	[2]	-	-	-	-	1.0	9.5	1.0	9.5	ns
		OE to B; no external load	[2]	-	-	-	-	1.0	10.7	1.0	9.6	ns
		OE to A		-	-	-	-	-	280	-	280	ns
		OE to B		-	-	-	-	-	220	-	220	ns
t <sub>t</sub>	transition	A port		-	-	-	-	0.7	4.5	0.7	4.5	ns
	time	B port		-	-	-	-	0.5	4.1	0.4	4.7	ns
t <sub>W</sub>	pulse width	data inputs		-	-	-	-	10	-	10	-	ns
f <sub>data</sub>	data rate			-	-	-	-	-	100	-	100	Mbp

### Table 12. Dynamic characteristics for temperature range -40 °C to +125 °C[1] ... continued

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7; for wave forms see Figure 5 and Figure 6.

 $t_t$  is the same as  $t_{THL}$  and  $t_{TLH}$ .

[2] Delay between OE going LOW and when the outputs are actually disabled.

Unit

pF

pF

pF

pF

pF

pF

pF

pF

### Dual supply translating transceiver; auto direction sensing; 3-state

#### Symbol Parameter Conditions V<sub>CC(A)</sub> 1.8 V 1.2 V 1.2 V 1.5 V 2.5 V 2.5 V 3.3 V V<sub>CC(B)</sub> 1.8 V 1.8 V 2.5 V 5.0 V 3.3 V 5.0 V 1.8 V to 5.0 V T<sub>amb</sub> = 25 °C outputs enabled; $OE = V_{CC(A)}$ C<sub>PD</sub> power dissipation A port: (direction A to B) 5 5 5 5 5 5 5 capacitance A port: (direction B to A) 8 8 8 8 8 8 8 B port: (direction A to B) 18 18 18 18 18 18 18 B port: (direction B to A) 13 12 12 12 12 13 16 outputs disabled; OE = GND A port: (direction A to B) 0.12 0.12 0.04 0.05 0.08 0.08 0.07 0.01 0.01 0.01 A port: (direction B to A) 0.01 0.01 0.01 0.01 B port: (direction A to B) 0.01 0.01 0.01 0.01 0.01 0.01 0.01 0.09 0.07 0.07 0.05 0.09 0.09 B port: (direction B to A) 0.07

# Table 13. Typical power dissipation capacitanceVoltages are referenced to GND (ground = 0 V).

[1]  $C_{PD}$  is used to determine the dynamic power dissipation (P<sub>D</sub> in  $\mu$ W).

 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma (C_L \times V_{CC}^2 \times f_o)$  where:

 $f_i$  = input frequency in MHz;

 $f_o = output frequency in MHz;$ 

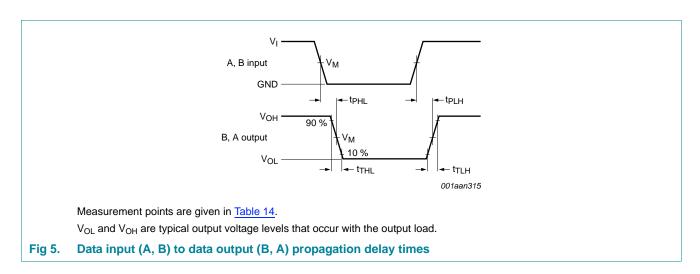
 $C_L$  = load capacitance in pF;

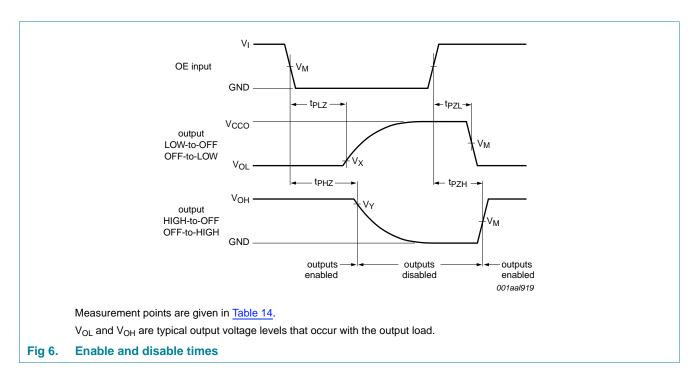
V<sub>CC</sub> = supply voltage in V;

N = number of inputs switching;

 $\Sigma(C_L \times V_{CC}{}^2 \times f_o)$  = sum of the outputs.

## 11. Waveforms

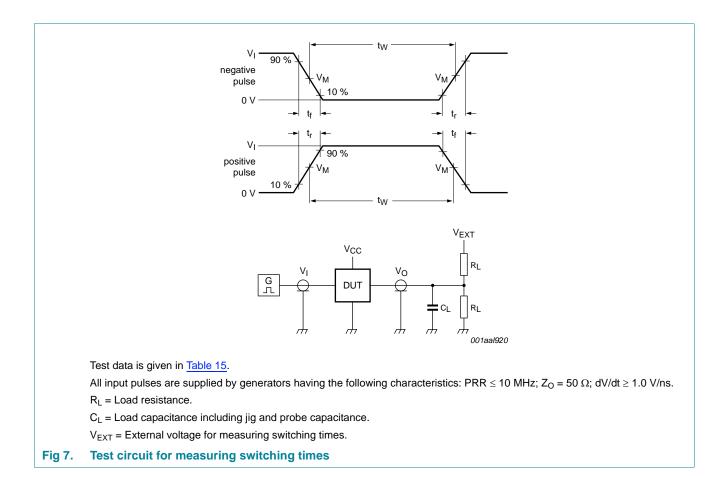




### Table 14. Measurement points<sup>[1]</sup>

Supply voltage	Input	Output	Output							
V <sub>cco</sub>	V <sub>M</sub>	V <sub>M</sub>	V <sub>X</sub>	V <sub>Y</sub>						
1.2 V	0.5V <sub>CCI</sub>	0.5V <sub>CCO</sub>	V <sub>OL</sub> + 0.1 V	V <sub>OH</sub> – 0.1 V						
$1.5~V\pm0.1~V$	0.5V <sub>CCI</sub>	0.5V <sub>CCO</sub>	V <sub>OL</sub> + 0.1 V	V <sub>OH</sub> – 0.1 V						
$1.8~V\pm0.15~V$	0.5V <sub>CCI</sub>	0.5V <sub>CCO</sub>	V <sub>OL</sub> + 0.15 V	V <sub>OH</sub> – 0.15 V						
$2.5~\textrm{V}\pm0.2~\textrm{V}$	0.5V <sub>CCI</sub>	0.5V <sub>CCO</sub>	V <sub>OL</sub> + 0.15 V	V <sub>OH</sub> – 0.15 V						
$3.3~V\pm0.3~V$	0.5V <sub>CCI</sub>	0.5V <sub>CCO</sub>	V <sub>OL</sub> + 0.3 V	V <sub>OH</sub> – 0.3 V						
$5.0~\text{V}\pm0.5~\text{V}$	0.5V <sub>CCI</sub>	0.5V <sub>CCO</sub>	V <sub>OL</sub> + 0.3 V	V <sub>OH</sub> – 0.3 V						

[1] V<sub>CCI</sub> is the supply voltage associated with the input and V<sub>CCO</sub> is the supply voltage associated with the output.



### Table 15. Test data

Supply voltag	le	Input		Load			V <sub>EXT</sub>			
V <sub>CC(A)</sub>	V <sub>CC(B)</sub>	VI <mark>[1]</mark>	∆t/∆V	CL	R <sub>L</sub> [2]	t <sub>PLH</sub> , t <sub>PHL</sub>	t <sub>PZH</sub> , t <sub>PHZ</sub>	t <sub>PZL</sub> , t <sub>PLZ</sub> [3]		
1.2 V to 3.6 V	1.65 V to 5.5 V	V <sub>CCI</sub>	$\leq$ 1.0 ns/V	15 pF	50 kΩ, 1 MΩ	open	open	2V <sub>CCO</sub>		

[1]  $V_{CCI}$  is the supply voltage associated with the input.

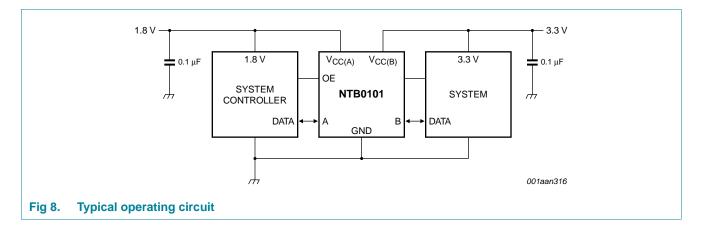
[2] For measuring data rate, pulse width, propagation delay and output rise and fall measurements,  $R_L = 1 \text{ M}\Omega$ ; for measuring enable and disable times,  $R_L = 50 \text{ k}\Omega$ .

[3] V<sub>CCO</sub> is the supply voltage associated with the output.

## **12. Application information**

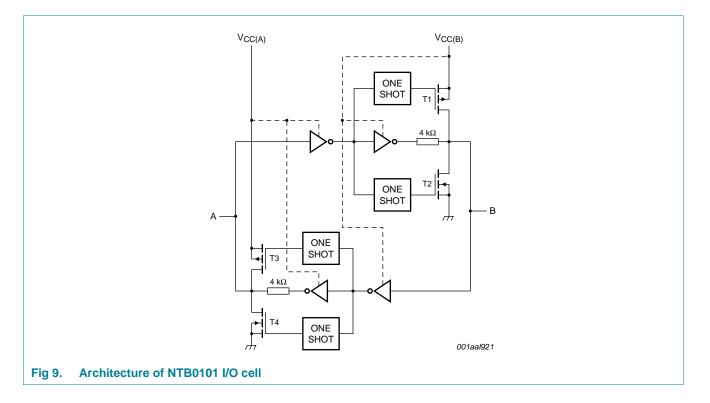
## **12.1 Applications**

Voltage level-translation applications. The NTB0101 can be used to interface between devices or systems operating at different supply voltages. See <u>Figure 8</u> for a typical operating circuit using the NTB0101.



## 12.2 Architecture

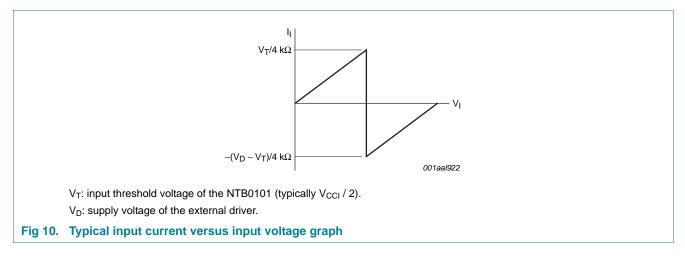
The architecture of the NTB0101 is shown in Figure 9. The device does not require an extra input signal to control the direction of data flow from A to B or from B to A. In a static state, the output drivers of the NTB0101 can maintain a defined output level, but the output architecture is designed to be weak, so that they can be overdriven by an external driver when data on the bus starts flowing in the opposite direction. The output of one-shot circuits detect rising or falling edges on the A or B ports. During a rising edge, the one-shot circuits turn on the PMOS transistors (T1, T3) for a short duration, accelerating the LOW-to-HIGH transition. Similarly, during a falling edge, the one-shot circuits turn on the NMOS transistors (T2, T4) for a short duration, accelerating the HIGH-to-LOW transition. During output transitions the typical output impedance is 70  $\Omega$  at V<sub>CCO</sub> = 1.2 V to 1.8 V, 50  $\Omega$  at V<sub>CCO</sub> = 1.8 V to 3.3 V and 40  $\Omega$  at V<sub>CCO</sub> = 3.3 V to 5.0 V.



**Product data sheet** 

## 12.3 Input driver requirements

For correct operation, the device driving the data I/Os of the NTB0101 must have a minimum drive capability of  $\pm 2$  mA See <u>Figure 10</u> for a plot of typical input current versus input voltage.



## 12.4 Power-up

During operation  $V_{CC(A)}$  must never be higher than  $V_{CC(B)}$ , however during power-up  $V_{CC(A)} \ge V_{CC(B)}$  does not damage the device, so either power supply can be ramped up first. There is no special power-up sequencing required. The NTB0101 includes circuitry that disables all output ports when either  $V_{CC(A)}$  or  $V_{CC(B)}$  is switched off.

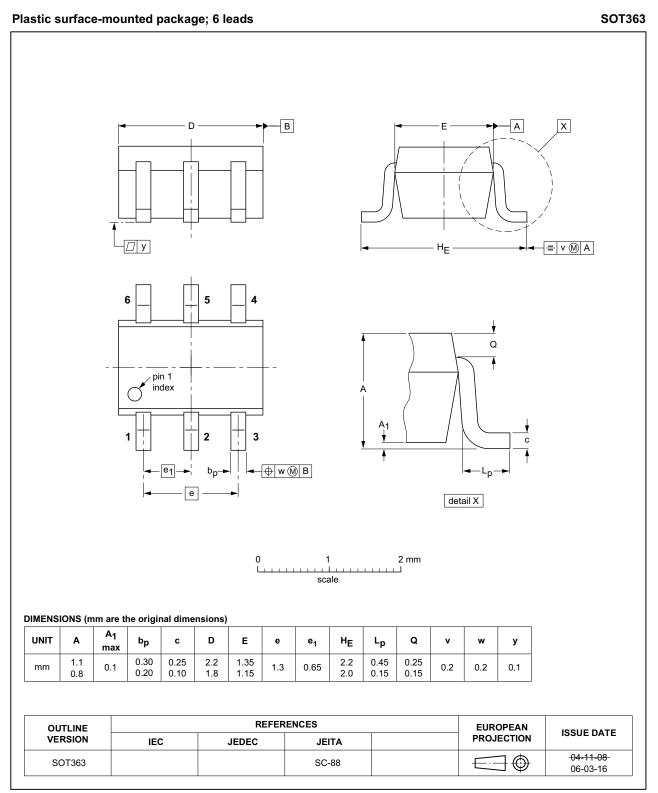
## 12.5 Enable and disable

An output enable input (OE) is used to disable the device. Setting OE = LOW causes all I/Os to assume the high-impedance OFF-state. The disable time ( $t_{dis}$  with no external load) indicates the delay between when OE goes LOW and when outputs actually become disabled. The enable time ( $t_{en}$ ) indicates the amount of time the user must allow for one one-shot circuitry to become operational after OE is taken HIGH. To ensure the high-impedance OFF-state during power-up or power-down, pin OE should be tied to GND through a pull-down resistor, the minimum value of the resistor is determined by the current-sourcing capability of the driver.

## 12.6 Pull-up or pull-down resistors on I/O lines

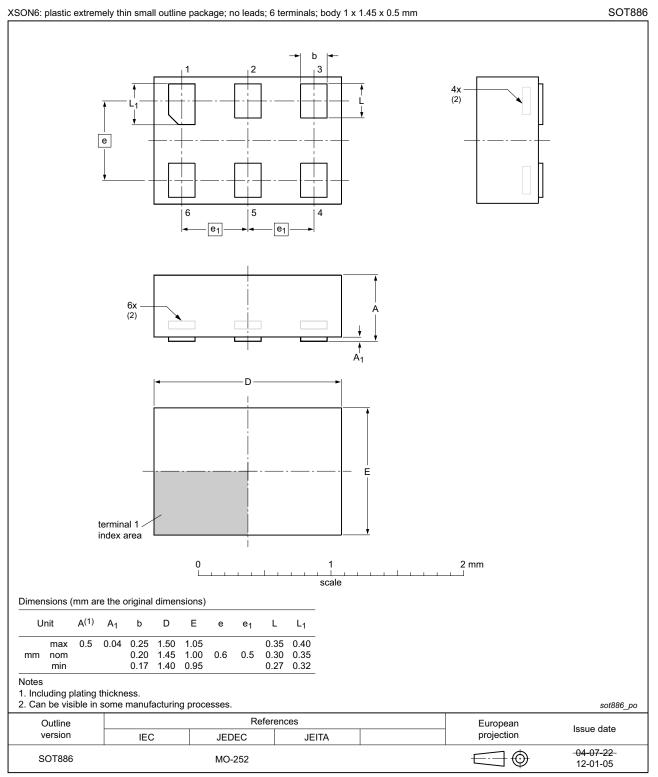
As mentioned previously the NTB0101 is designed with low static drive strength to drive capacitive loads of up to 70 pF. To avoid output contention issues, any pull-up or pull-down resistors used must be above 50 k $\Omega$ . For this reason the NTB0101 is not recommended for use in open drain driver applications such as 1-Wire or I<sup>2</sup>C-bus. For these applications, the NTS0101 level translator is recommended.

## 13. Package outline

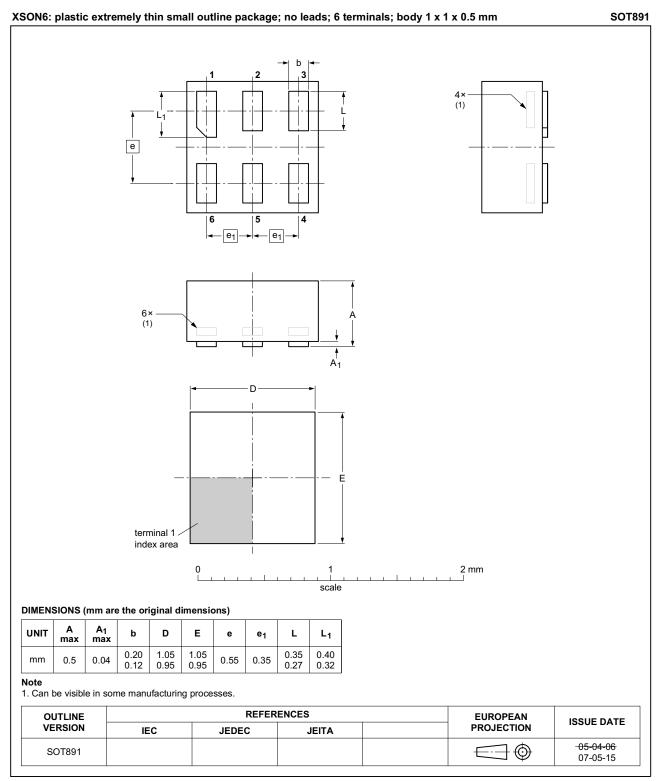


### Fig 11. Package outline SOT363 (SC-88)

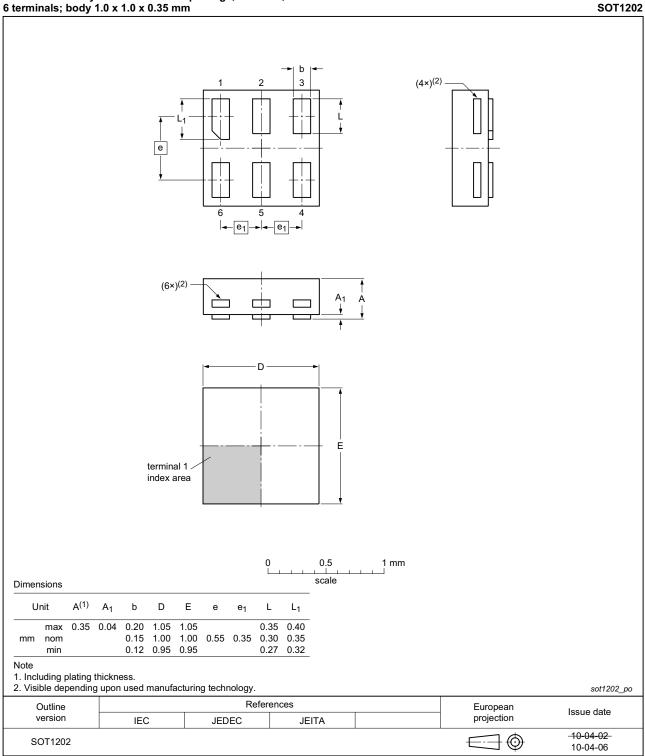
**Product data sheet** 



### Fig 12. Package outline SOT886 (XSON6)



## Fig 13. Package outline SOT891 (XSON6)



XSON6: extremely thin small outline package; no leads; 6 terminals; body 1.0 x 1.0 x 0.35 mm

### Fig 14. Package outline SOT1202 (XSON6)

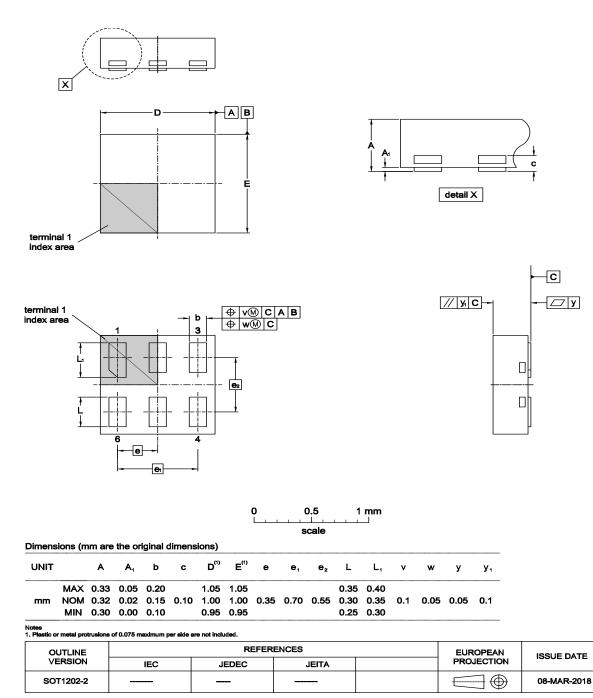
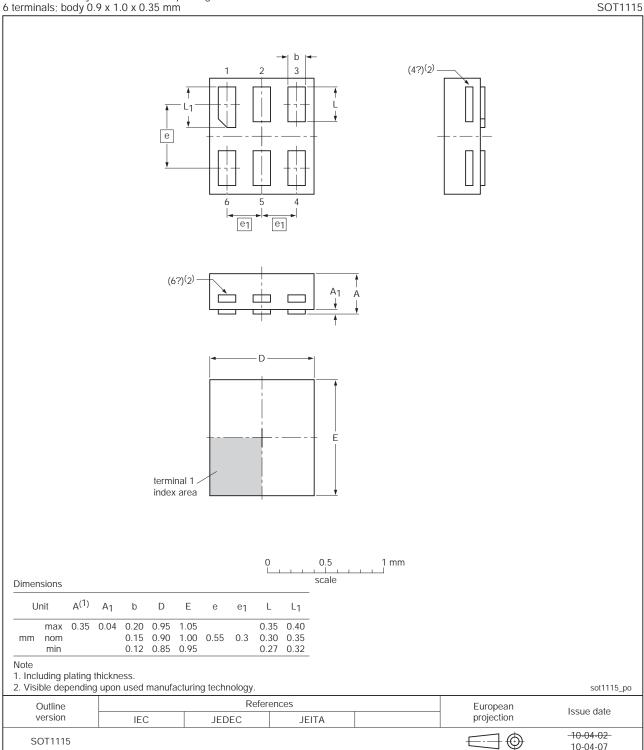


Fig 15. Package outline SOT1202-2 (X2SON6)



### XSON6: extremely thin small outline package; no leads; 6 terminals; body 0.9 x 1.0 x 0.35 mm

Fig 16. Package outline SOT1115 (XSON6)

## **14. Abbreviations**

Table 16. Abbr	eviations
Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
NMOS	N-type Metal Oxide Semiconductor
PMOS	P-type Metal Oxide Semiconductor
PRR	Pulse Repetition Rate

## **15. Revision history**

## Table 17.Revision history

NTB0101 v.7       20180409       Product data sheet       NTB0101 v         Modifications:       • Corrected Figure 15 "Package outline SOT1202-2 (X2SON6)"       • Table 2 "Ordering options"         -       Updated orderable part number, packing method and minimum order quant NTB0101GS1         NTB0101 v.6       20180301       Product data sheet       NTB0101 v         Modifications:       • Added NTB0101GS1       NTB0101GS1	es
• Table 2 "Ordering options"       –       Updated orderable part number, packing method and minimum order quant NTB0101GS1         NTB0101 v.6       20180301       Product data sheet       NTB0101 v         Modifications:       •       Added NTB0101GN and NTB0101GS1       NTB0101GS1	/.6
-       Updated orderable part number, packing method and minimum order quant NTB0101GS1         NTB0101 v.6       20180301       Product data sheet       NTB0101 v         Modifications:       •       Added NTB0101GN and NTB0101GS1	
NTB0101GS1       NTB0101 v.6     20180301     Product data sheet     NTB0101 v       Modifications:        • Added NTB0101GN and NTB0101GS1	
Modifications: • Added NTB0101GN and NTB0101GS1	tity for
	/.5
<ul> <li><u>Section 3 "Ordering information"</u></li> </ul>	
<ul> <li>Updated table notes for <u>Table 1 "Device information"</u></li> </ul>	
<ul> <li>Added <u>Section 3.1 "Ordering options"</u></li> </ul>	
NTB0101 v.5 20160224 Product data sheet NTB0101 v	.4
Modifications:  • Deleted NTB0101GV	
NTB0101 v.4 20120806 Product data sheet - NTB0101 v	/.3
Modifications: • Package outline drawing of SOT886 (Figure 12) modified.	
NTB0101 v.3 2011110 Product data sheet - NTB0101 v	.2
Modifications:  • Legal pages updated.	
NTB0101 v.2 20110505 Product data sheet - NTB0101 v	/1
NTB0101 v.1 20101230 Product data sheet	

## **16. Legal information**

## 16.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

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## **18. Contents**

1	General description 1
2	Features and benefits 1
3	Ordering information 2
3.1	Ordering options 2
4	Functional diagram 3
5	Pinning information
5.1	Pinning
5.2	Pin description 3
6	Functional description 4
7	Limiting values 4
8	Recommended operating conditions 4
9	Static characteristics 5
10	Dynamic characteristics 7
11	Waveforms 12
12	Application information
12.1	Applications 15
12.2	Architecture 16
12.3	Input driver requirements 17
12.4	Power-up 17
12.5	Enable and disable 17
12.6	Pull-up or pull-down resistors on I/O lines 17
13	Package outline 18
14	Abbreviations 24
15	Revision history 24
16	Legal information
16.1	Data sheet status 25
16.2	Definitions 25
16.3	Disclaimers
16.4	Trademarks 26
17	Contact information 26
18	Contents 27

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